

Search History. (app.) *[Signature]* (4/29/05).

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|---|---|------------------|---------|------------------|
| L1 | 5 | ((("5,906,680") or ("6,190,975") or ("20010160605") or ("5,683,934") or ("20020016085") or ("6,306,211"))).PN. | US-PGPUB; USPAT | OR | OFF | 2005/04/29 07:11 |
| L2 | 59 | (US-20010015170-\$ or US-20020016085-\$ or US-20020094658-\$ or US-20020102862-\$ or US-20020124793-\$ or US-20020158311-\$ or US-20020158313-\$ or US-20020160605-\$ or US-20020182423-\$ or US-20020192918-\$ or US-20030054601-\$ or US-20040089918-\$ or US-20040161875-\$ or US-20040195655-\$ or US-20040198010-\$ or US-20040217430-\$ or US-20050006663-\$ or US-20050023642-\$ or US-20050051798-\$ or US-20050064645-\$ or US-20050082571-\$).did. or (US-5296258-\$ or US-5298452-\$ or US-5449923-\$ or US-5456762-\$ or US-5459089-\$ or US-5599403-\$ or US-5670414-\$ or US-5671914-\$ or US-5681402-\$ or US-5683934-\$ or US-5726440-\$ or US-5847418-\$ or US-5861324-\$ or US-5906680-\$ or US-6064081-\$ or US-6183857-\$ or US-6190975-\$ or US-6214107-\$ or US-6273950-\$ or US-6285064-\$ or US-6306211-\$ or US-6358773-\$ or US-6362065-\$ or US-6368888-\$ or US-6472594-\$ or US-6552375-\$).did. or (US-6673662-\$ or US-6750119-\$). did. or (JP-62216364-\$).did. or (DE-3777507-\$ or EP-703628-\$ or EP-829908-\$ or EP-908984-\$ or EP-1039512-\$ or US-20020016085-\$ or US-6285064-\$ or US-6358773-\$ or US-20020102862-\$).did. | US-PGPUB; USPAT; JPO; DERWENT | OR | OFF | 2005/04/29 07:14 |
| L3 | 0 | ("2andkanazawa.in.").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/29 07:14 |

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| L4 | 0 | 2 and kanazawa.in. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/29 07:15 |
| L5 | 2 | 2 and nakazawa.in. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/29 07:15 |
| L6 | 2120 | ((257/77) or (257/183) or (257/197) or (257/198) or (438/931)).CCLS. | US-PGPUB; USPAT | OR | OFF | 2005/04/29 08:04 |
| L7 | 355 | 6 and silicon adj carbide and boron | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/29 07:31 |
| L8 | 10 | 6 and silicon adj carbide and boron and (uhv ultra adj "high" adj vacuum) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/29 08:05 |
| L9 | 2300 | ((257/77) or (257/78) or (257/183) or (257/197) or (257/198) or (438/931)).CCLS. | US-PGPUB; USPAT | OR | OFF | 2005/04/29 08:04 |
| L10 | 180 | 9 NOT 6 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/29 08:05 |
| L11 | 0 | 10 and silicon adj carbide and boron and (uhv ultra adj "high" adj vacuum) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/29 08:05 |
| S1 | 4 | "775514".ap. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/29 07:11 |
| S2 | 6 | ((("6,285,064") or ("6,358,773") or ("6,368,888"))).PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/03 22:06 |
| S3 | 1 | (US-20040161875-\$).did. | US-PGPUB | OR | OFF | 2005/04/03 22:08 |

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| S4 | 10 | (silicon adj carbide sic) near20 graded near20 buffer and single adj (crystalline crystal) near4 (silicon si) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/03 22:13 |
| S5 | 2 | (silicon adj carbide sic) near20 graded near20 buffer and single adj (crystalline crystal) near4 (silicon si) and (thick thickness) near10 buffer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/03 22:18 |
| S6 | 2 | ("6750119").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/03 22:18 |
| S7 | 1 | "5683934".PN. | USPAT; USOCR | OR | OFF | 2005/04/03 22:19 |
| S8 | 1 | "5906680".PN. | USPAT; USOCR | OR | OFF | 2005/04/03 22:19 |
| S9 | 1 | "6190975".PN. | USPAT; USOCR | OR | OFF | 2005/04/03 22:20 |
| S10 | 1 | "20020160605".PN. | US-PGPUB | OR | OFF | 2005/04/03 22:20 |
| S11 | 155 | junction near4 (sic silicon adj carbide) near4 (si silicon) and (monocrystalline single adj (crystal crystalline)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/04 09:50 |
| S12 | 15 | (US-20010015170-\$).did. or (US-6472594-\$ or US-6273950-\$ or US-6214107-\$ or US-6183857-\$ or US-5861324-\$ or US-5847418-\$ or US-5726440-\$ or US-5681402-\$ or US-5671914-\$ or US-5599403-\$ or US-5459089-\$ or US-5456762-\$ or US-5449923-\$).did. or (JP-62216364-\$).did. | US-PGPUB; USPAT; JPO | OR | OFF | 2005/04/04 09:49 |
| S13 | 144 | S11 and (interface thick thickness abrupt sharp buffer) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/04 09:51 |
| S14 | 14 | S12 and (interface thick thickness abrupt sharp buffer) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/04 09:51 |
| S15 | 7 | S12 and (interface thick thickness abrupt sharp buffer) and ("SiC/Si" "Si/SiC") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/04 10:13 |

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| S16 | 3 | ((("5298452") or ("5906680"))).PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/04 10:01 |
| S17 | 0 | (257/77anduhf-cvdand("S/SiC""SiC/S")).CCLS. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/04 10:02 |
| S18 | 0 | 257/77 and uhf-cvd and ("S/SiC""SiC/S") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/04 10:02 |
| S19 | 0 | 257/77 and uhf-cvd and ("S/SiC""SiC/S") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/04 10:02 |
| S20 | 0 | 257/77 and uhf near1 cvd | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/04 10:03 |
| S21 | 0 | 257/77 and uhf adj cvd | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/04 10:03 |
| S22 | 0 | 257/77.ccls. and uhf adj cvd | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/04 10:03 |
| S23 | 3 | 257/77.ccls. and uhf and cvd | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/04 10:03 |
| S24 | 1260 | ((257/77) or (438/931)).CCLS. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/29 07:26 |
| S25 | 47 | S24 and ("Si/SiC" "SiC/S" interface junction) near10 (abrupt sharp) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/04 10:24 |

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| S26 | 5 | S24 and hbt and buffer and graded and (thick thickness thin) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/04 11:40 |
| S27 | 0 | (single adj (crystalline crystal) monocrystalline) near3 (silicon "Si") near6 (silicon adj carbide "SiC") and graded near4 ("Si.sub."\$3"C.sub."\$3) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/04 11:44 |
| S28 | 363 | (single adj (crystalline crystal) monocrystalline) near1 (silicon "Si") near2 substrate near6 (silicon adj carbide "SiC") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/04 11:45 |
| S29 | 0 | (single adj (crystalline crystal) monocrystalline) near1 (silicon "Si") near2 substrate near6 (silicon adj carbide "SiC") and (buffer graded) near4 ("Si.sub.xC.sub.1-x" "Si.sub.1-xC.sub.x") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/04 11:46 |
| S30 | 0 | (single adj (crystalline crystal) monocrystalline) near1 (silicon "Si") near2 substrate near6 (silicon adj carbide "SiC") and "Si.sub."\$3"C.sub."\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/04 11:47 |
| S31 | 363 | (single adj (crystalline crystal) monocrystalline) near1 (silicon "Si") near2 substrate near6 (silicon adj carbide "SiC") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/04 11:48 |
| S32 | 179 | (single adj (crystalline crystal) monocrystalline) near1 (silicon "Si") near2 substrate near6 (silicon adj carbide "SiC") not (silicon adj carbide adj substrate) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/04 12:19 |
| S33 | 10 | ((("5,906,680") or ("6,190,975") or ("20010160605") or ("5,683,934") or ("20020016085") or ("6,306,211"))).PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/04 12:24 |
| S34 | 10 | ((("5,906,680") or ("6,190,975") or ("5,683,934") or ("20020016085") or ("6,306,211"))).PN. or (2001/0160605).CCLS. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/04 12:24 |
| S35 | 0 | ("20010160605").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/04 12:25 |

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| S36 | 0 | (2001/0160605).CCLS. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/04 12:25 |
| S37 | 85 | kanazawa.in. and 200210\$2.pd. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/04 12:26 |
| S38 | 273 | kanazawa.in. and silicon | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/04 12:26 |
| S39 | 31 | kanazawa.in. and silicon | US-PGPUB | OR | OFF | 2005/04/04 12:31 |
| S40 | 26 | kanazawa.in. and silicon and substrate | US-PGPUB | OR | OFF | 2005/04/04 12:26 |
| S41 | 0 | @pd=200210\$2 and kanazawa.in. | US-PGPUB | OR | OFF | 2005/04/04 12:31 |
| S42 | 202 | kanazawa.in. | US-PGPUB | OR | OFF | 2005/04/04 12:32 |
| S43 | 4 | suemitsu.in. and sic adj film | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/04 12:53 |
| S44 | 0 | suemitsu.in. and nakazaka.in. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/04 12:53 |
| S45 | 4 | suemitsu.in. and nakazawa.in. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/04 12:59 |
| S46 | 0 | ("20010160605").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/04 12:58 |
| S47 | 2 | ("2001160605").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/04 12:58 |
| S48 | 15481 | nakazawa.in. | US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/04 12:59 |

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| S49 | 125 | nakazawa.in. and 200210\$2.pd. | US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/04 13:01 |
| S50 | 187 | nakazawa.in. and substrate | US-PGPUB | OR | OFF | 2005/04/04 13:57 |
| S51 | 0 | (2004/0161875).CCLS. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/04 13:57 |
| S52 | 2 | ("20040161875").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/04 13:58 |
| S53 | 2 | ("20070161875").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/04 13:58 |
| S54 | 0 | ("20010160605").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/04 13:59 |
| S55 | 0 | ("(monocrystallinesingleadjcrystal) near2(siliconSi)and(carbonC)and(c oncentrationprofile)").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/27 10:25 |
| S56 | 8580 | (monocrystalline single adj crystal) near2 (silicon Si) and (carbon C) and (concentration profile) and boron | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/27 10:26 |
| S57 | 1322 | (monocrystalline single adj crystal) near2 (silicon Si) and (carbon C) and (concentration profile) and boron near5 (barrier diffusion) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/27 10:26 |
| S58 | 85 | (monocrystalline single adj crystal) near2 (silicon Si) and (carbon C) and (concentration profile) and boron near5 (barrier diffusion) and (hbt heterojunction adj bipolar adj transistor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/27 10:27 |
| S59 | 456 | gated adj diode | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/27 12:14 |

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| S60 | 73 | gated adj diode.ti. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/27 12:15 |
| S61 | 3 | "751714".ap. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/27 12:16 |
| S62 | 46 | boron near1 diffusion and (silicon adj carbide SiC) and concentration near3 profile and (silicon Si) near3 substrate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/28 08:55 |
| S63 | 0 | intrinsic adj buffer near3 (silicon si) near6 (crystalline monocrystalline single adj crystal) and hbt | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/28 08:57 |
| S64 | 188 | buffer near3 (silicon si) near6 (crystalline monocrystalline single adj crystal) and hbt | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/28 09:23 |
| S65 | 0 | collector near4 lattice and S64 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/28 09:23 |
| S66 | 0 | collector near10 lattice and S64 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/28 09:23 |
| S67 | 8 | collector near10 lattice and S62 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/28 10:23 |
| S68 | 27 | (single adj crystalline monocrystalline) near2 emitter and hbt | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/28 10:32 |
| S69 | 1 | (single adj crystalline monocrystalline) near2 emitter near5 (mobility conductivity resistivity) and hbt | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/28 11:05 |

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|-----|----|--|---|----|-----|------------------|
| S70 | 13 | (single adj crystalline monocrystalline) near2 emitter near5 (mobility conductivity resistivity) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/28 11:05 |
| S71 | 88 | polycrystalline near3 emitter and hbt | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/28 12:44 |
| S72 | 27 | polycrystalline near3 emitter and hbt and (carbide SiC) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/28 12:45 |
| S73 | 1 | polycrystalline near3 (carbide SiC) near4 emitter and hbt and (carbide SiC) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/28 12:46 |
| S74 | 1 | polycrystalline near3 (carbide SiC) near4 emitter and hbt | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/28 12:46 |
| S75 | 2 | ("6137120").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/28 13:09 |
| S76 | 95 | fang.in. and emitter | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/28 13:10 |